



Anton Persson

Postdoctoral Scholar, Electrical Engineering

Bio

BIO

Anton Persson is a postdoctoral researcher in the Electrical Engineering Department at Stanford University, supervised by Professor Eric Pop. Prior to joining Stanford, he received his PhD in Electrical Engineering from Lund University, Sweden, in 2023 and his M.Sc. in Engineering Physics from Chalmers University of Technology, Sweden, in 2018. At Stanford, he researches emerging memristor technologies for in-memory computing applications, including phase change materials and ferroelectrics integrated onto 2D-materials.

PROFESSIONAL EDUCATION

- Doctor of Philosophy, Lunds Universitet (2023)
- PhD, Lund University , Electrical Engineering (2023)
- M.Sc., Chalmers University of Technology , Engineering Physics (2018)

STANFORD ADVISORS

- Eric Pop, Postdoctoral Faculty Sponsor

LINKS

- LinkedIn: <https://www.linkedin.com/in/a-persson/>
- Pop Lab research website: <http://poplab.stanford.edu/>
- Google Scholar: <https://scholar.google.com/citations?hl=en&user=g9vGpgUAAAAJ>

Publications

PUBLICATIONS

- **Reconfigurable signal modulation in a ferroelectric tunnel field-effect transistor** *NATURE COMMUNICATIONS*
Zhu, Z., Persson, A. O., Wernersson, L.
2023; 14 (1): 2530
- **Sensing single domains and individual defects in scaled ferroelectrics** *SCIENCE ADVANCES*
Zhu, Z., Persson, A. O., Wernersson, L.
2023; 9 (5): eade7098
- **Ferroelectric-Antiferroelectric Transition of Hf1-XZrXO2 on Indium Arsenide with Enhanced Ferroelectric Characteristics for Hf0.2Zr0.8O2** *ACS APPLIED ELECTRONIC MATERIALS*
Dahlberg, H., Persson, A. O., Athle, R., Wernersson, L.
2022; 4 (12): 6357-6363

- **Improved Endurance of Ferroelectric HfxZr1-xO2 Integrated on InAs Using Millisecond Annealing** *ADVANCED MATERIALS INTERFACES*
Athle, R., Blom, T., Irish, A., Persson, A. O., Wernersson, L., Timm, R., Borg, M.
2022; 9 (27)
- **As-deposited ferroelectric HZO on a III-V semiconductor** *APPLIED PHYSICS LETTERS*
Andersen, A., Persson, A. O., Wernersson, L.
2022; 121 (1)
- **Integration of Ferroelectric HfxZr1-xO2 on Vertical III-V Nanowire Gate-All-Around FETs on Silicon** *IEEE ELECTRON DEVICE LETTERS*
Persson, A. O., Zhu, Z., Athle, R., Wernersson, L.
2022; 43 (6): 854-857
- **Top Electrode Engineering for Freedom in Design and Implementation of Ferroelectric Tunnel Junctions Based on Hf1-xZrxO2** *ACS APPLIED ELECTRONIC MATERIALS*
Athle, R., Persson, A. O., Troian, A., Borg, M.
2022; 4 (3): 1002-1009
- **Effects of TiN Top Electrode Texturing on Ferroelectricity in Hf1-xZrxO2** *ACS APPLIED MATERIALS & INTERFACES*
Athle, R., Persson, A. O., Irish, A., Menon, H., Timm, R., Borg, M.
2021; 13 (9): 11089-11095
- **A method for estimating defects in ferroelectric thin film MOSCAPs** *APPLIED PHYSICS LETTERS*
Persson, A. O., Athle, R., Svensson, J., Borg, M., Wernersson, L.
2020; 117 (24)
- **Reduced annealing temperature for ferroelectric HZO on InAs with enhanced polarization** *APPLIED PHYSICS LETTERS*
Persson, A. O., Athle, R., Littow, P., Persson, K., Svensson, J., Borg, M., Wernersson, L.
2020; 116 (6)
- **Multidimensional Hybridization of Dark Surface Plasmons** *ACS NANO*
Yankovich, A. B., Verre, R., Olsen, E., Persson, A. O., Trinh, V., Dovner, G., Kall, M., Olsson, E.
2017; 11 (4): 4265-4274